

Fig. 1(a)

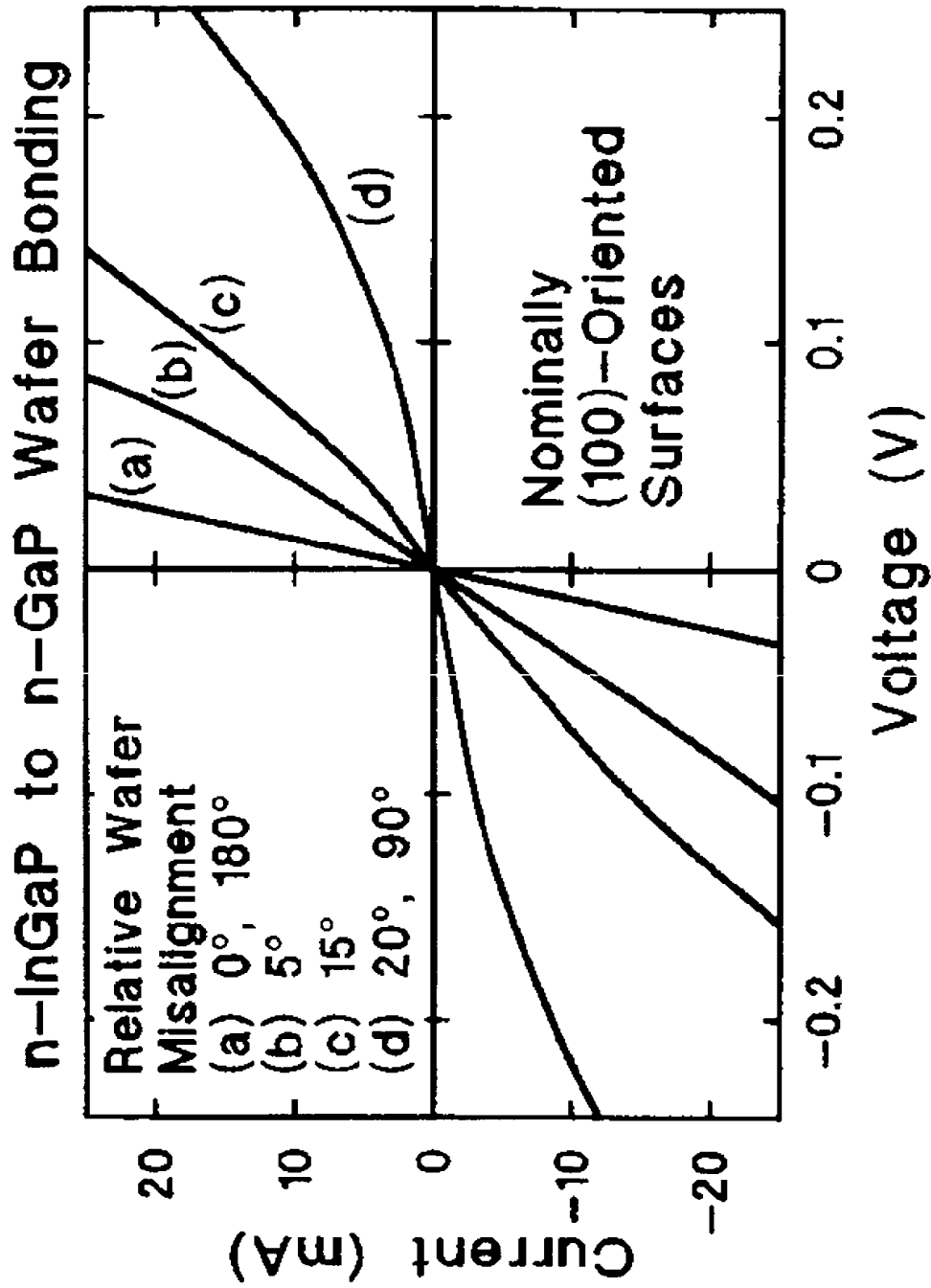


Fig. 1(b)

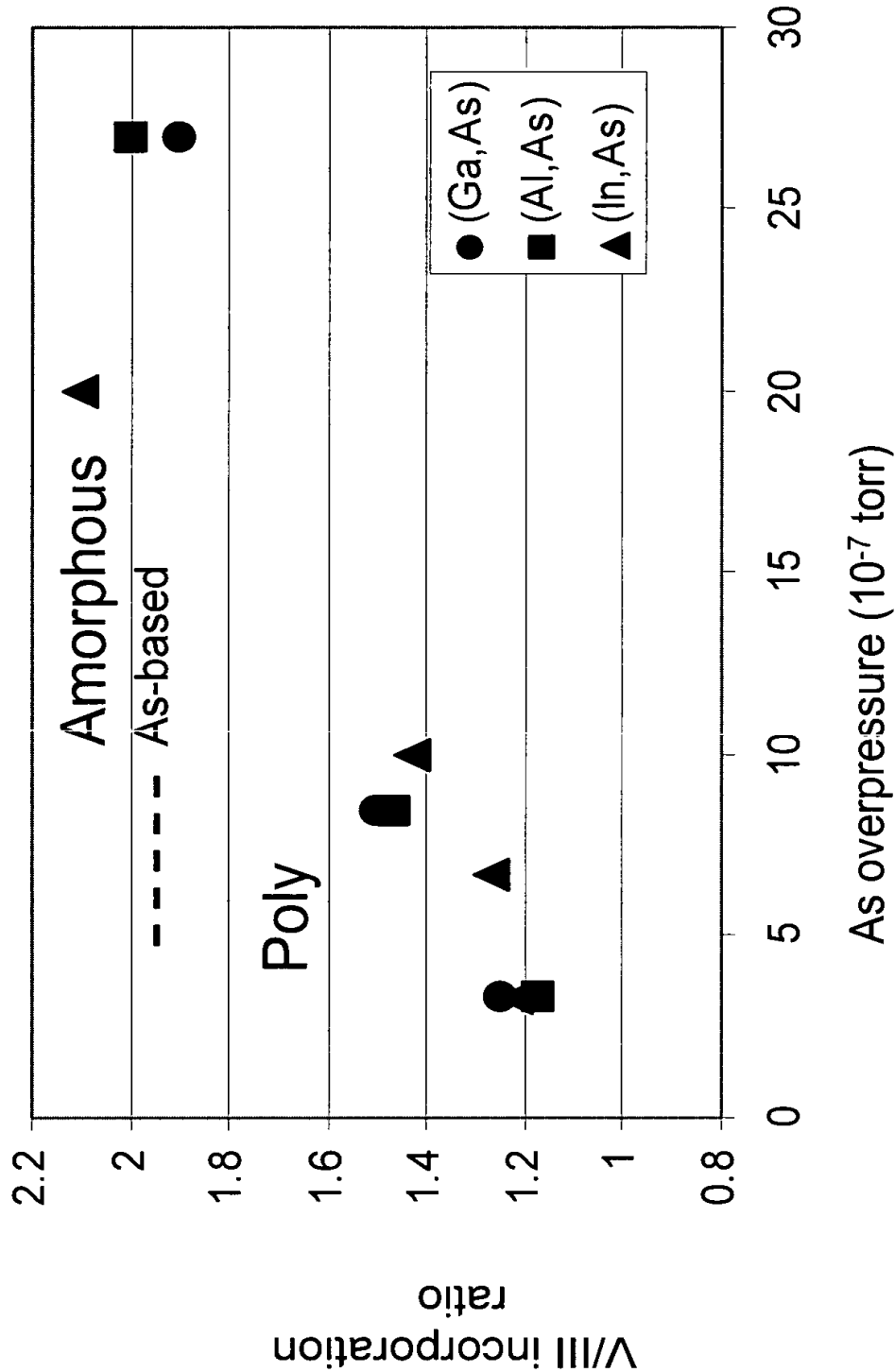


Fig. 2(a)

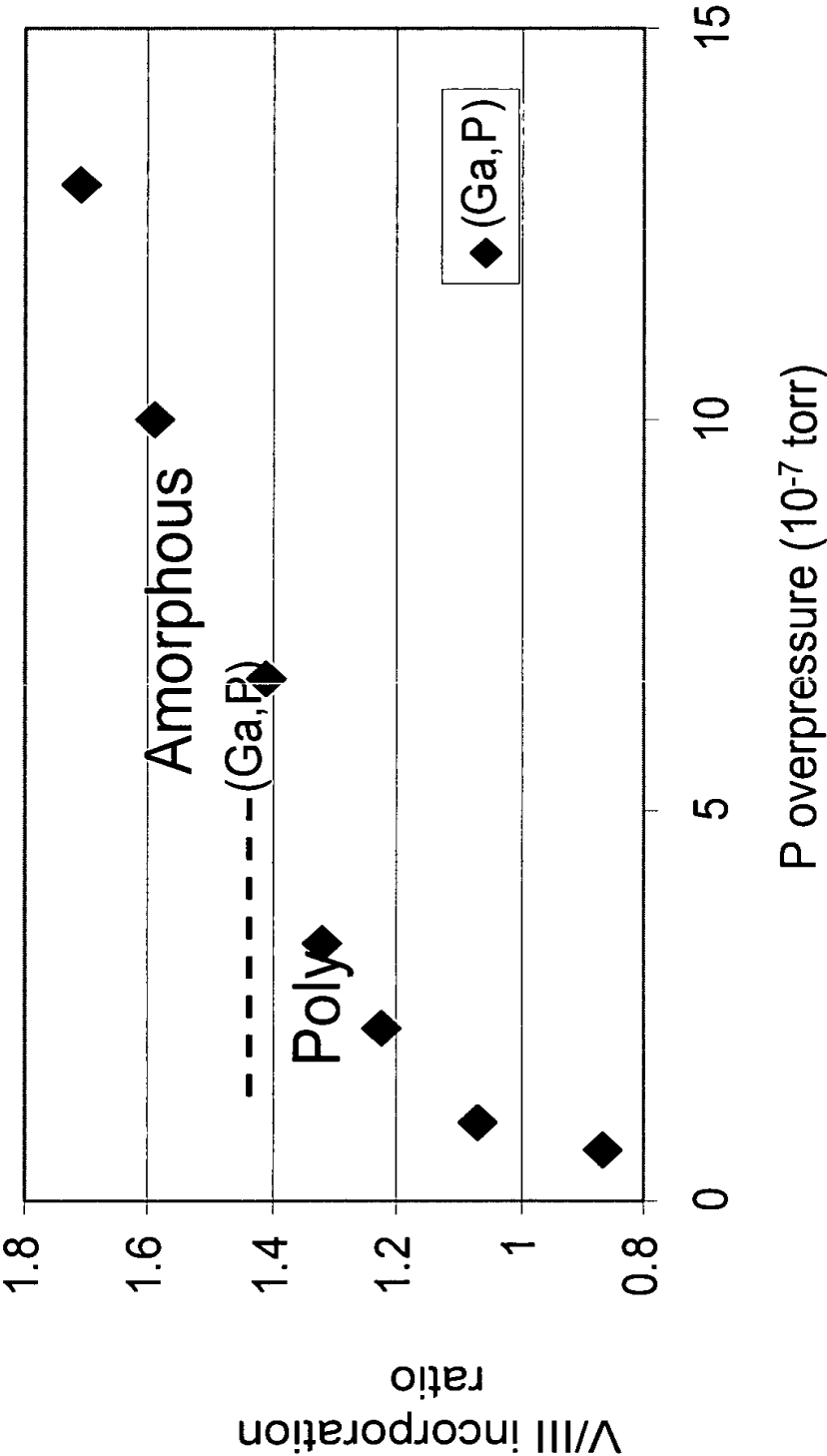
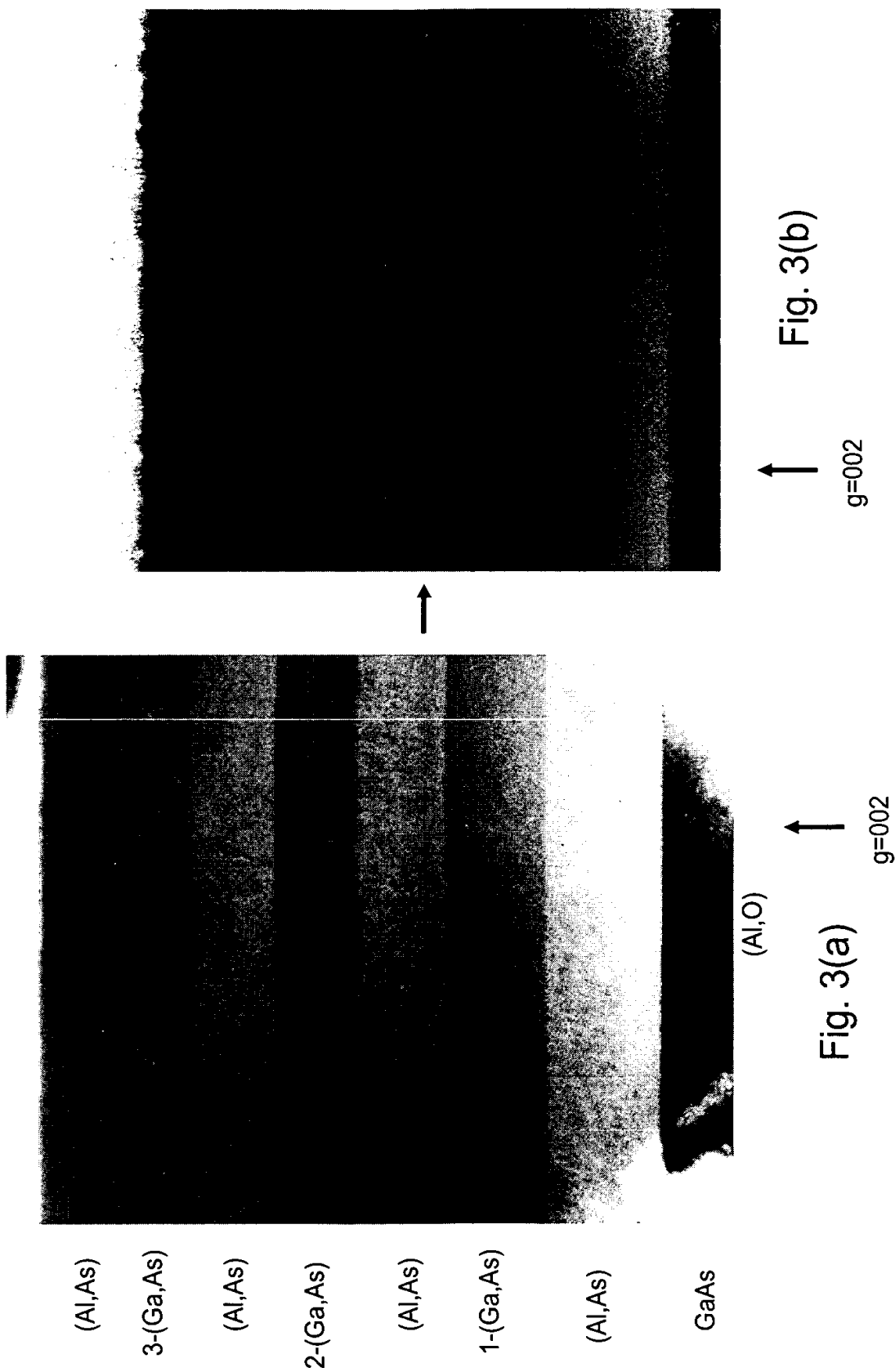


Fig. 2(b)



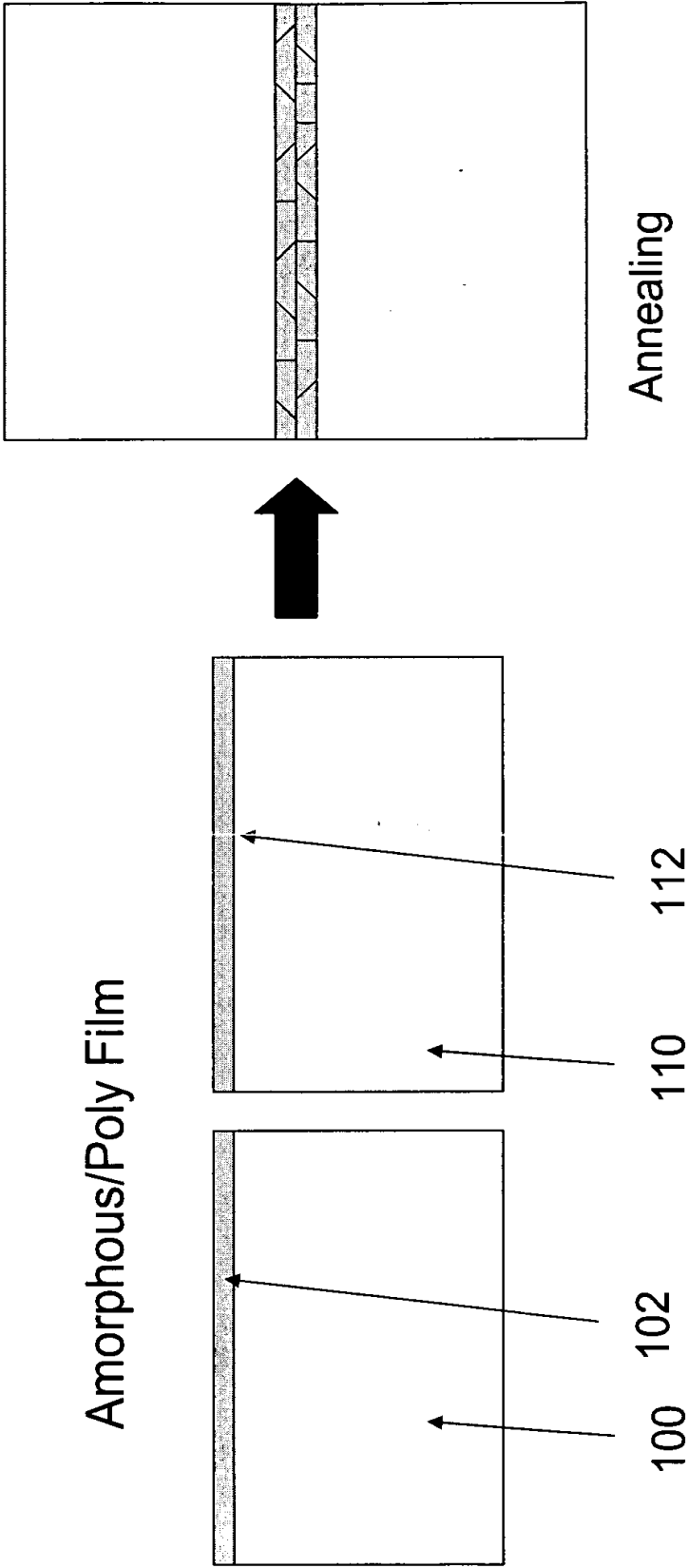


Fig. 4

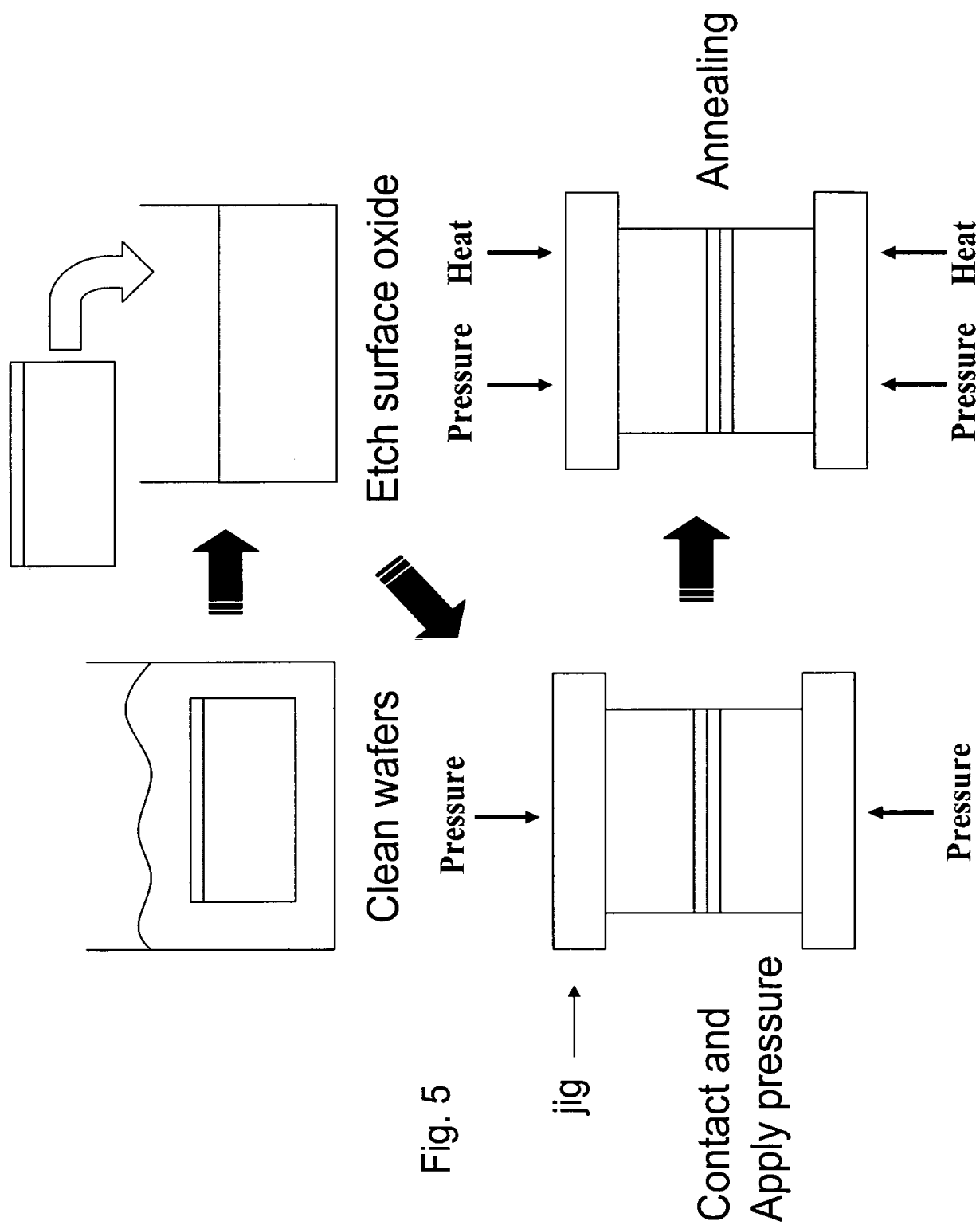


Fig. 5

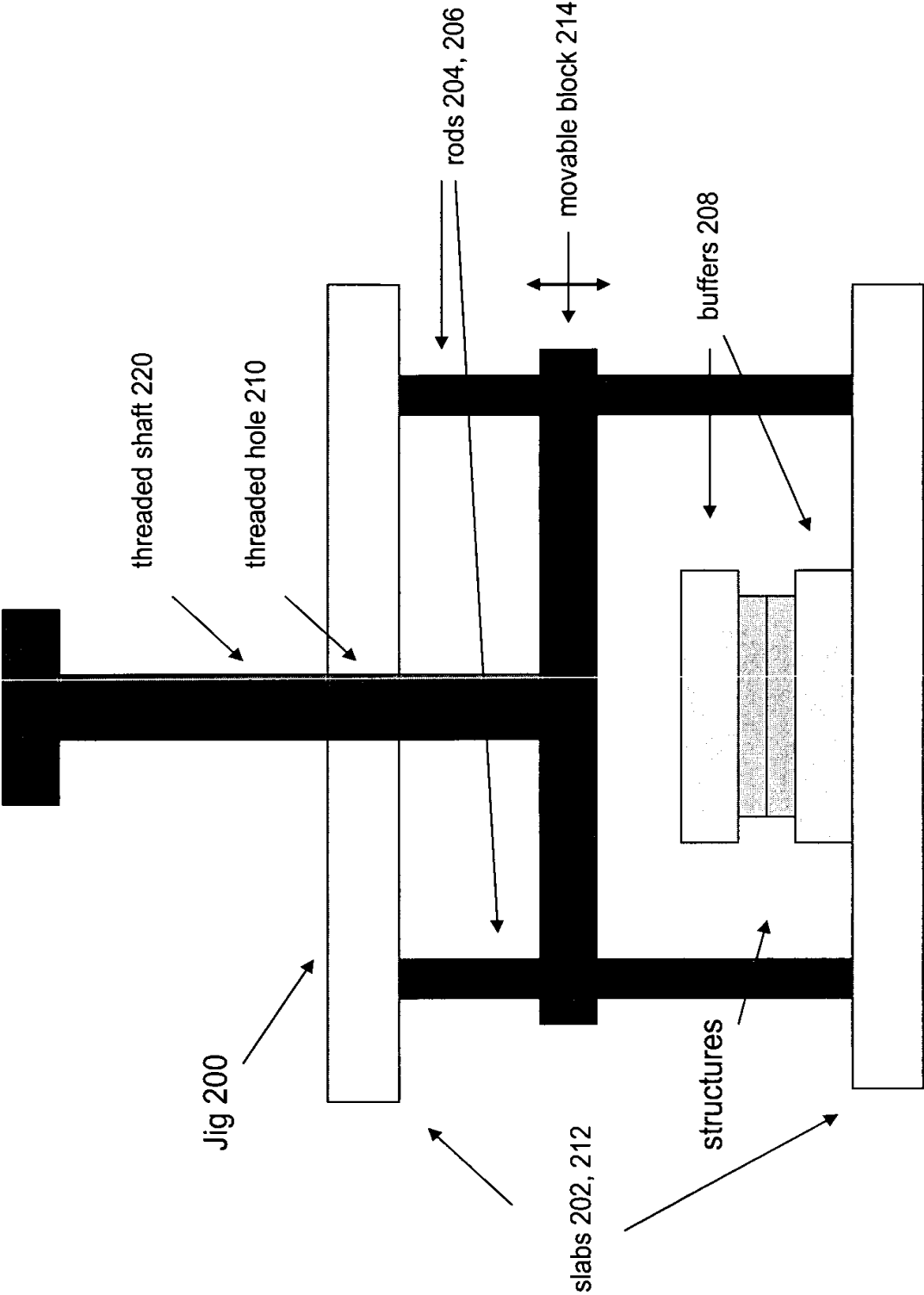
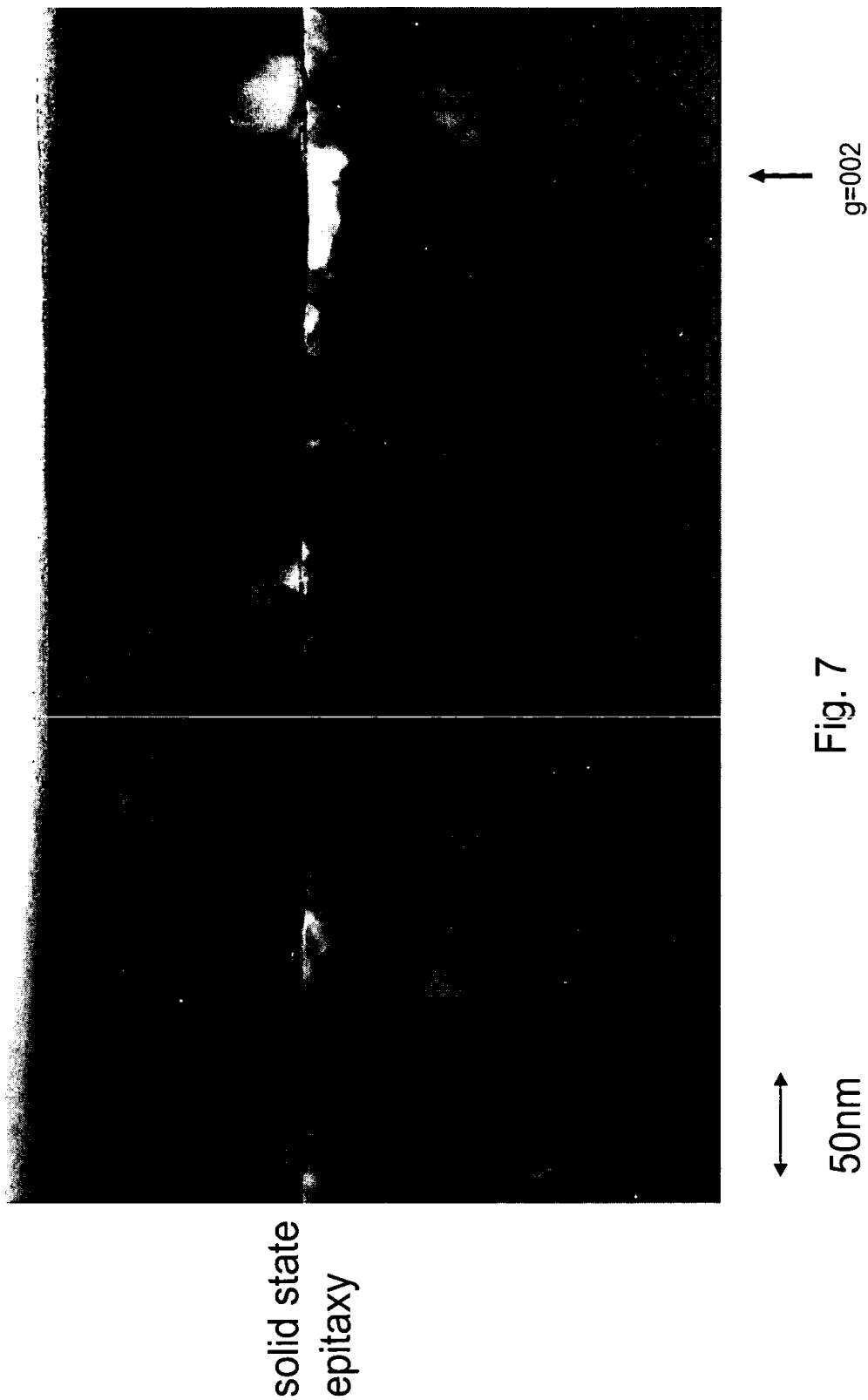


Fig. 6



Amorphous (Ga,P) bonding
Anneal at 600 °C for 10 hrs

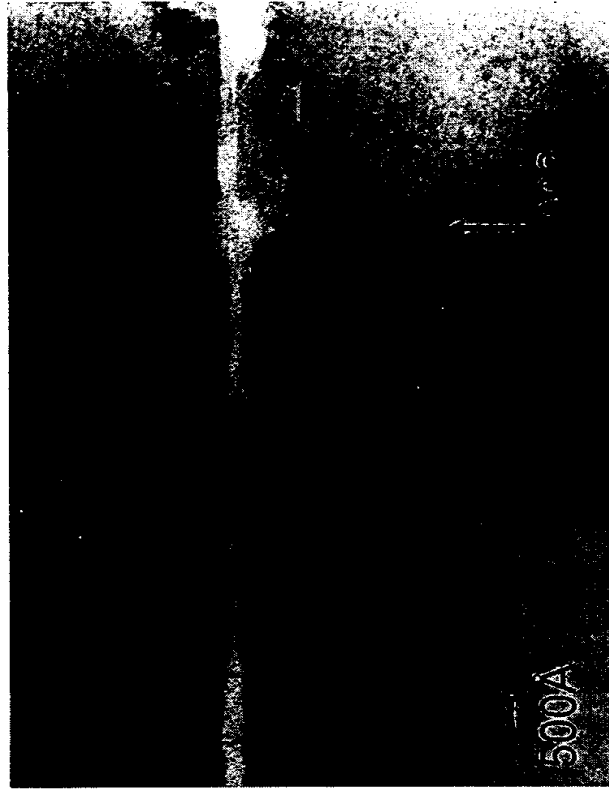


Fig. 8(b)

Polycrystalline (Ga,P) bonding
Anneal at 600 °C for 9 hrs

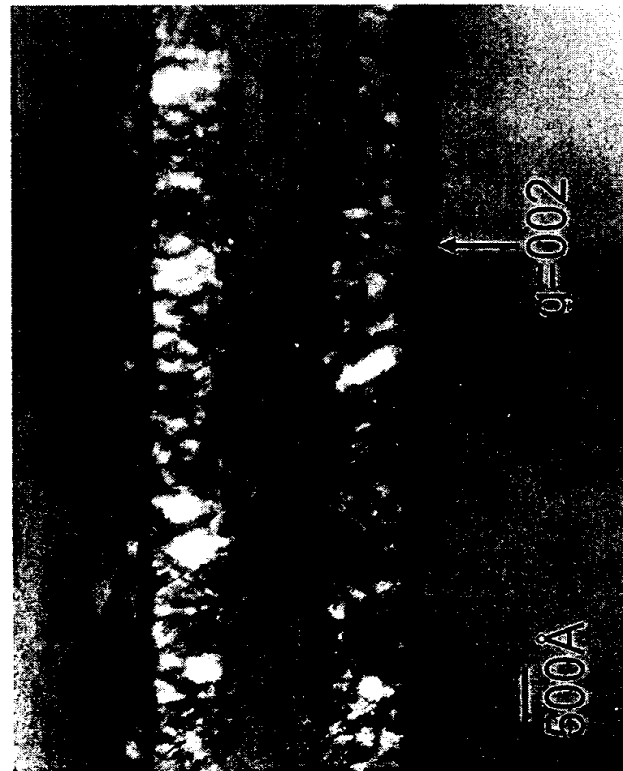


Fig. 8(a)

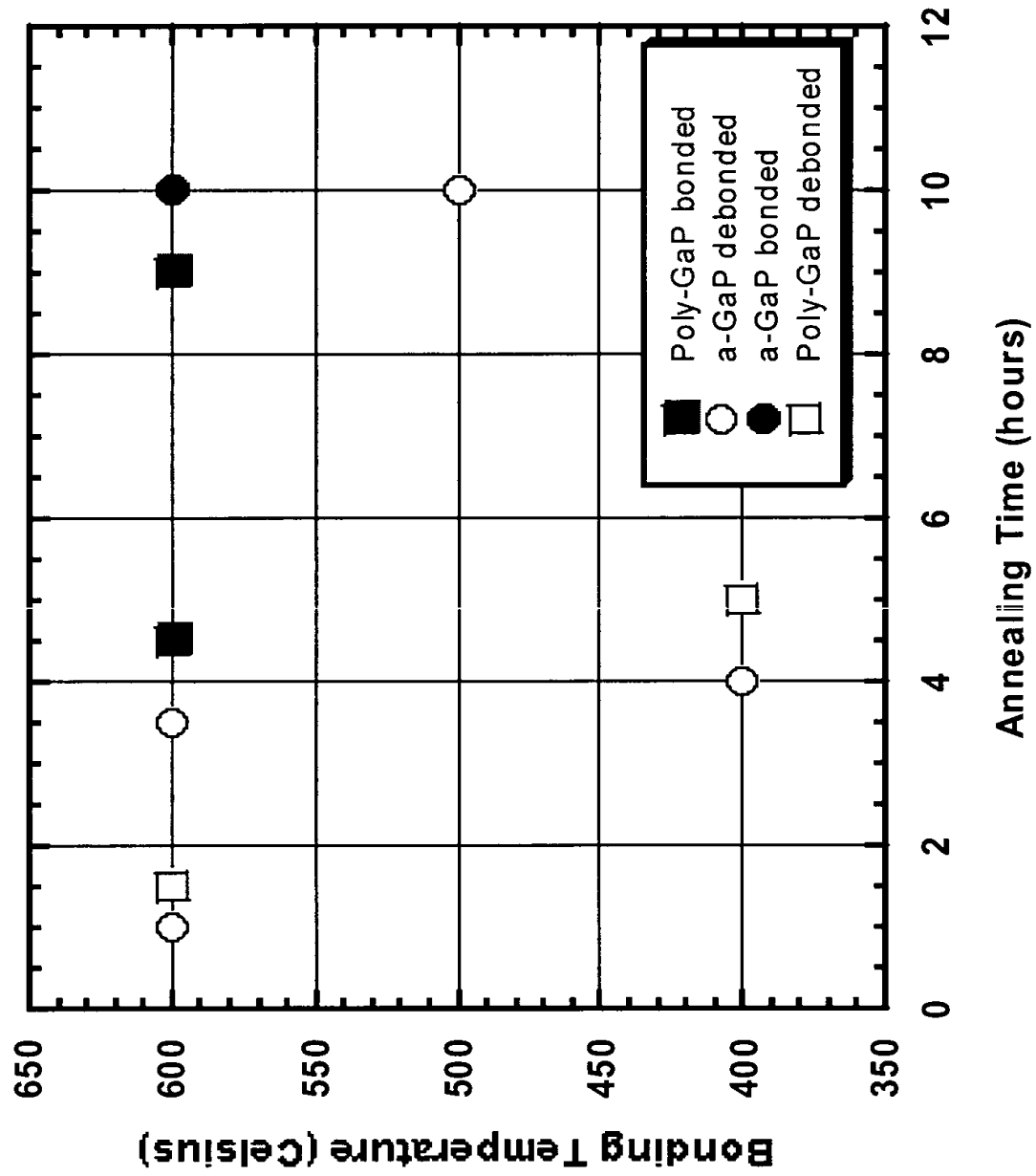


Fig. 9

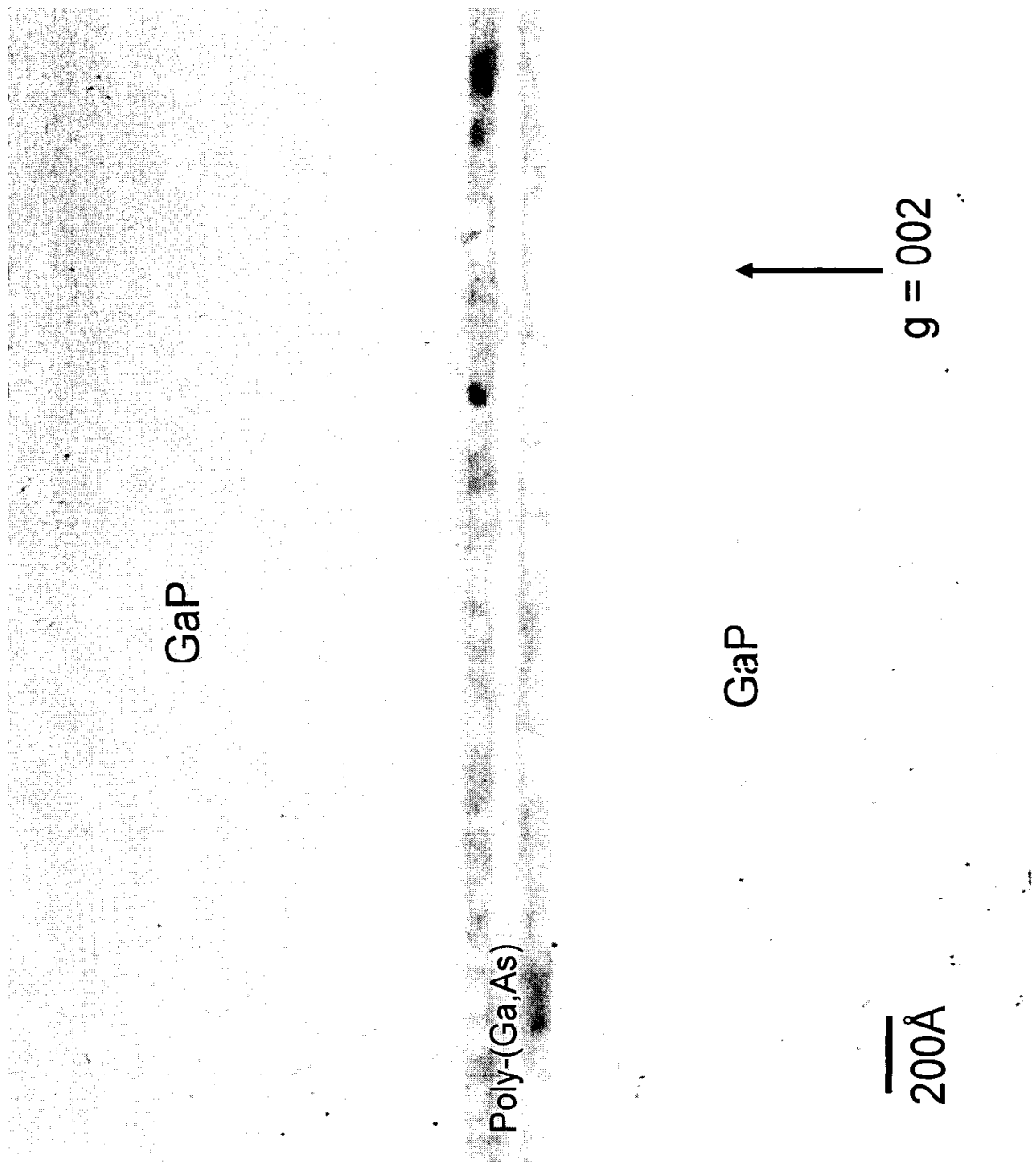


Fig. 10

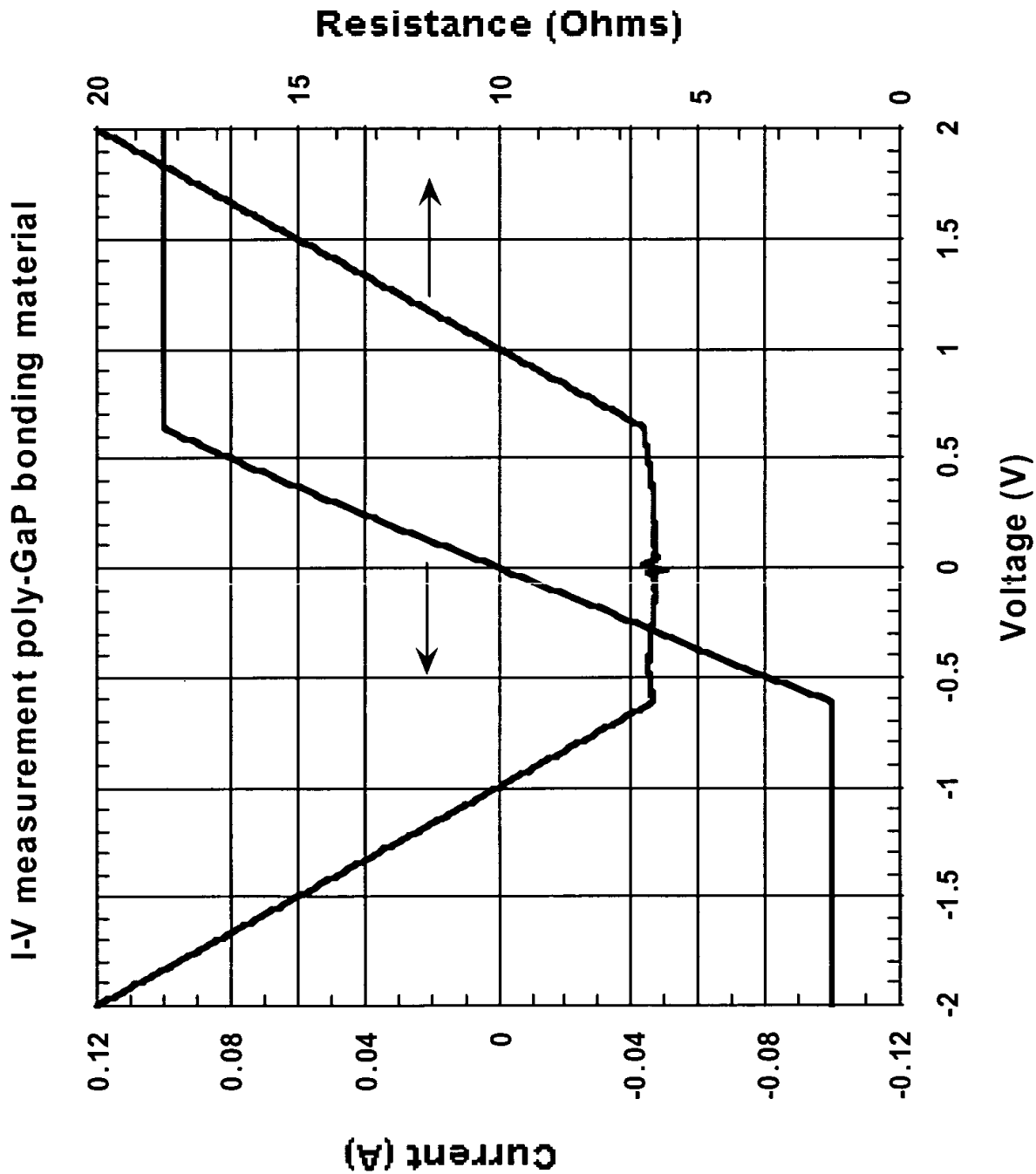


Fig. 11(a)

I-V measurement amorphous GaP bonding material

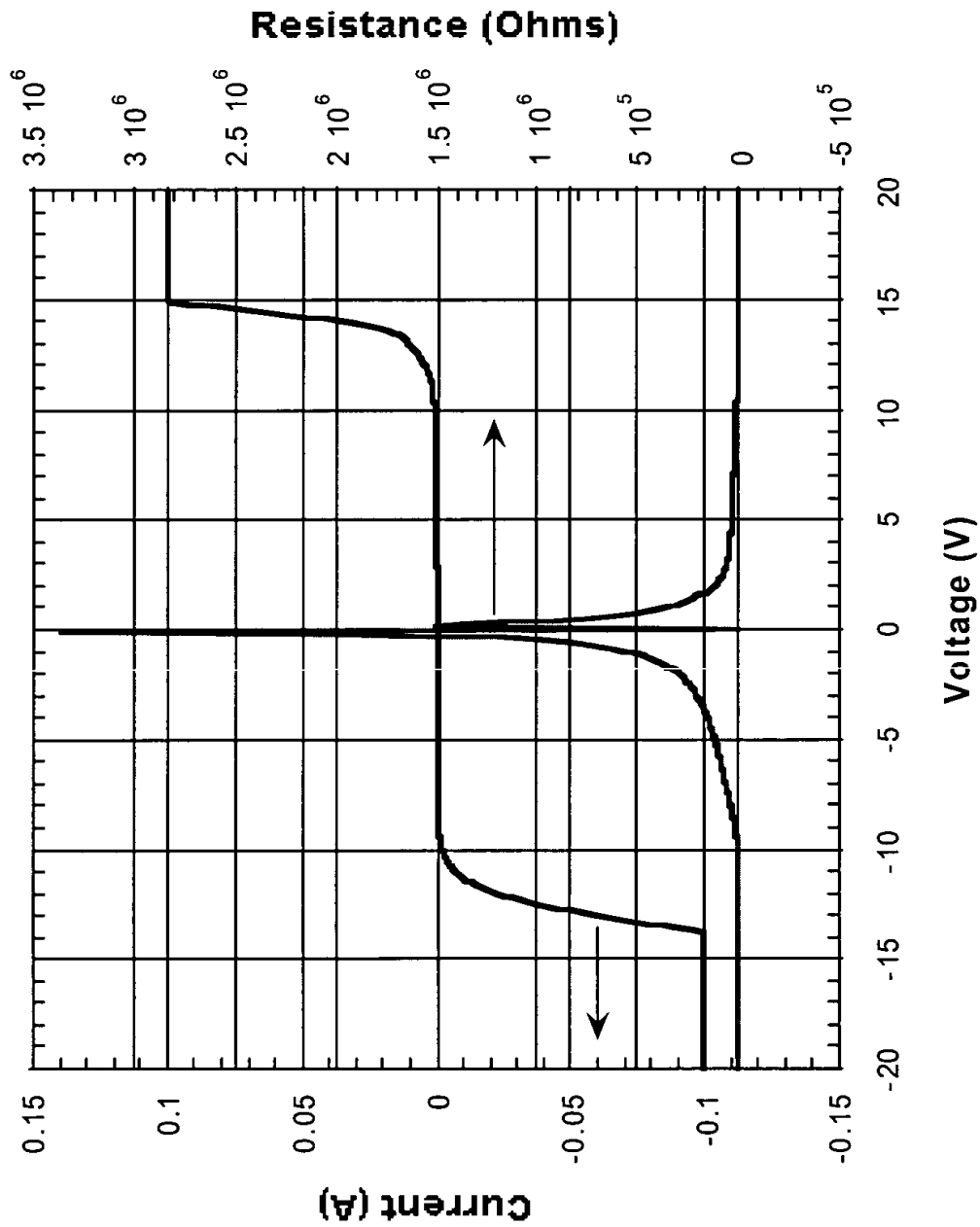


Fig. 11(b)

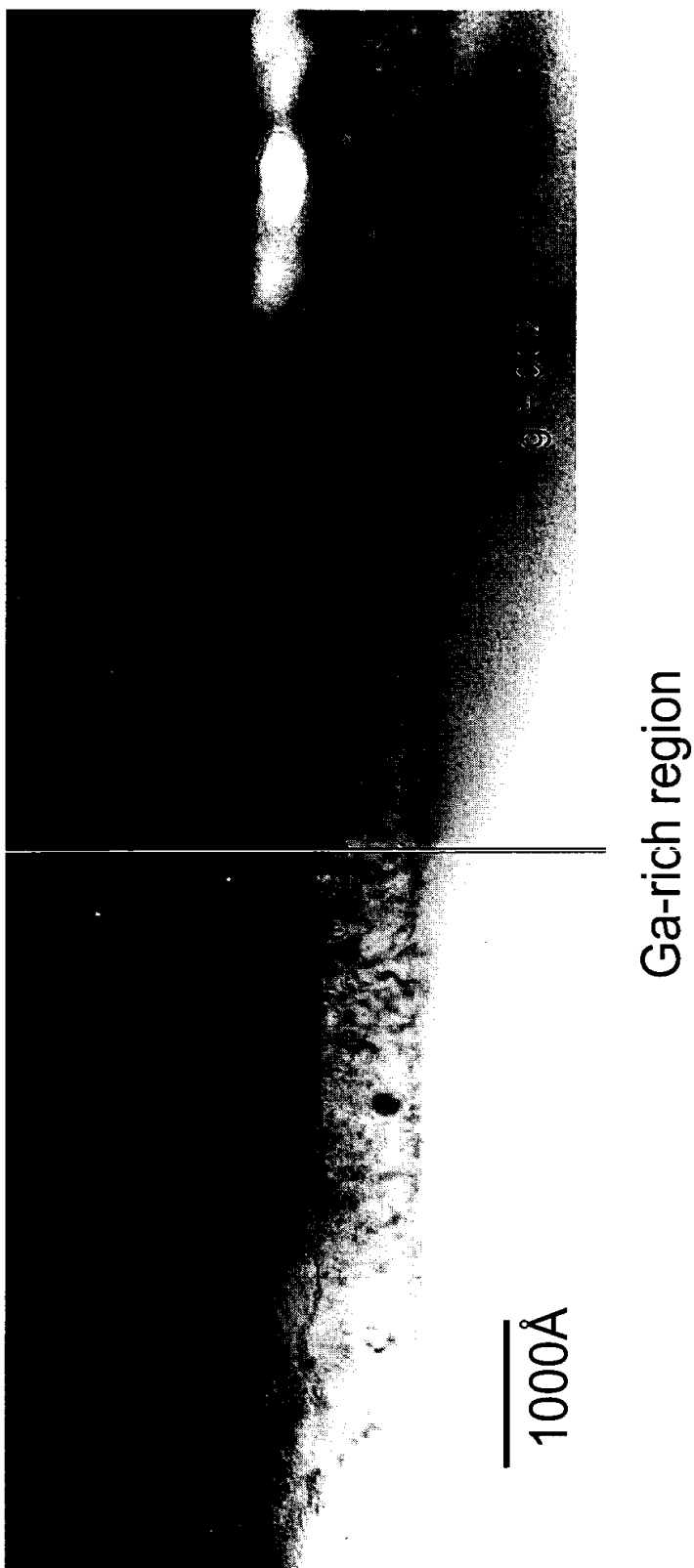


Fig. 12

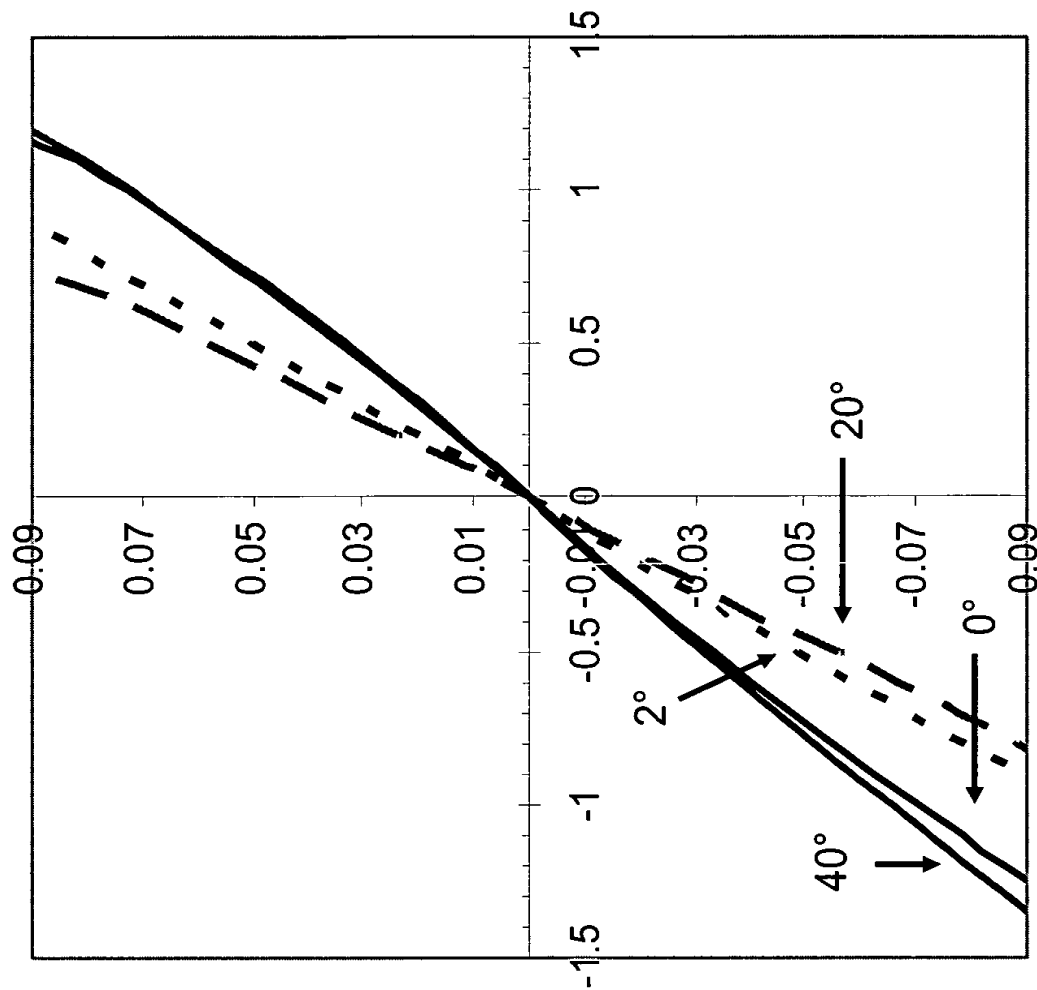


Fig. 13

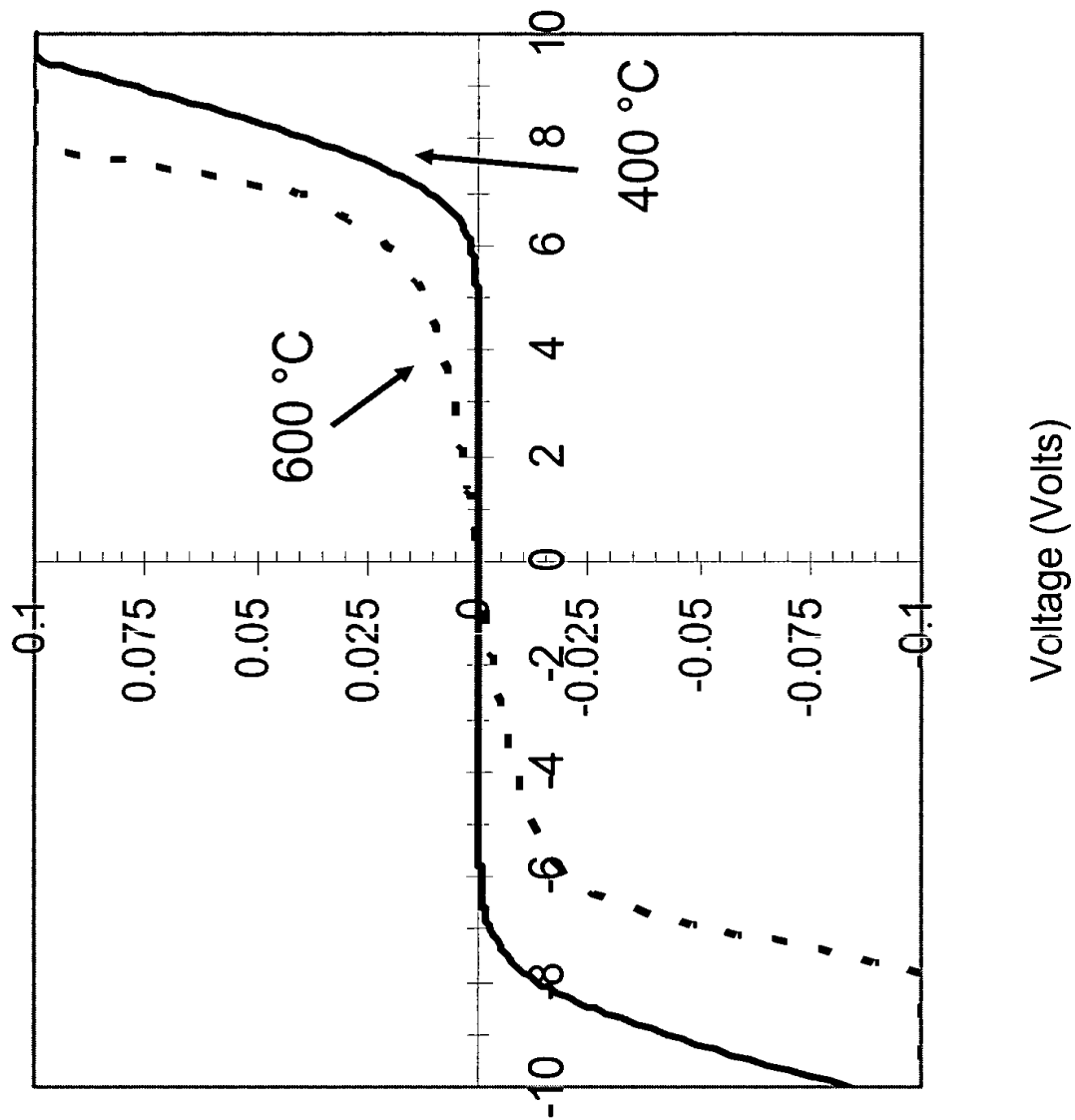


Fig. 14

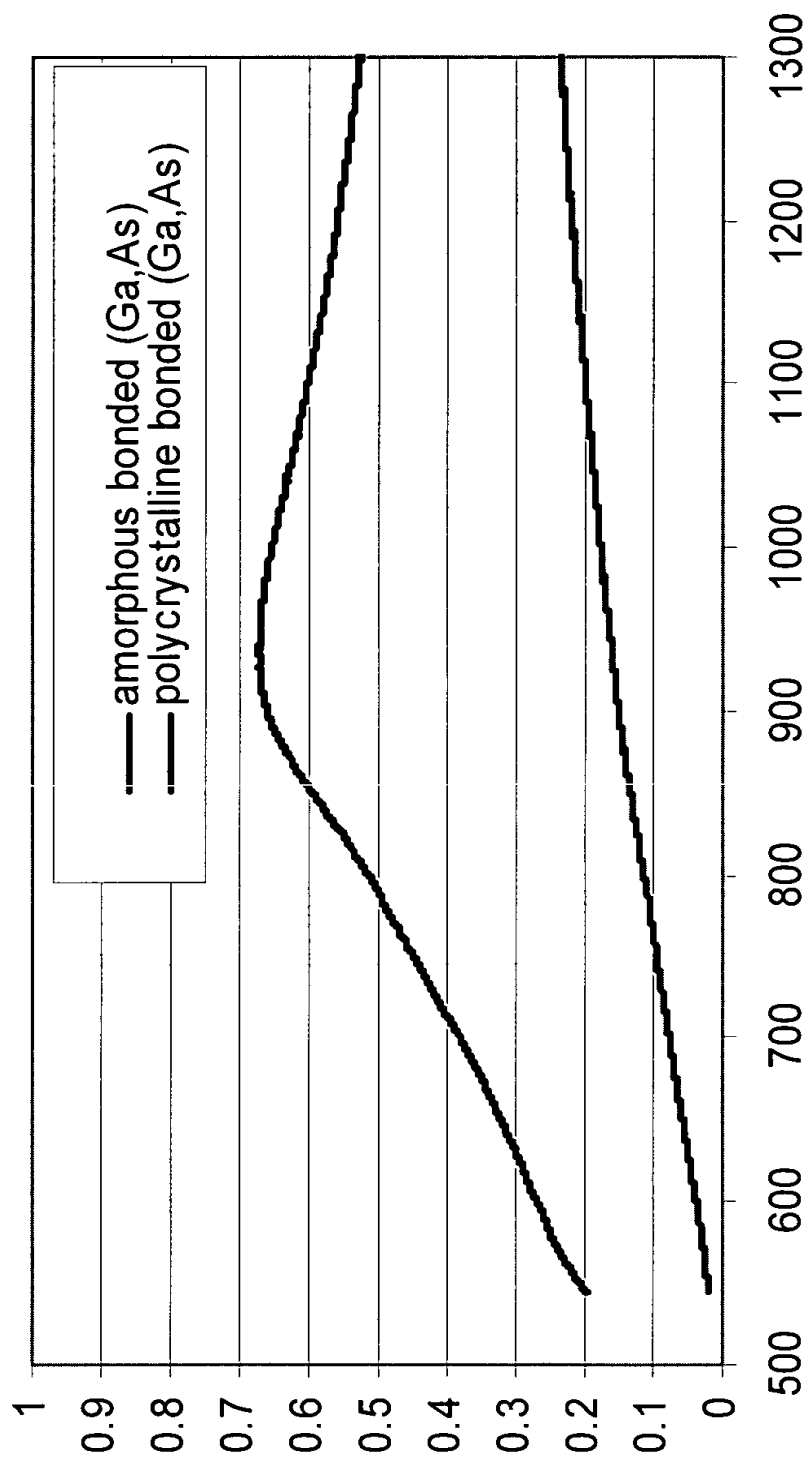


Fig. 15

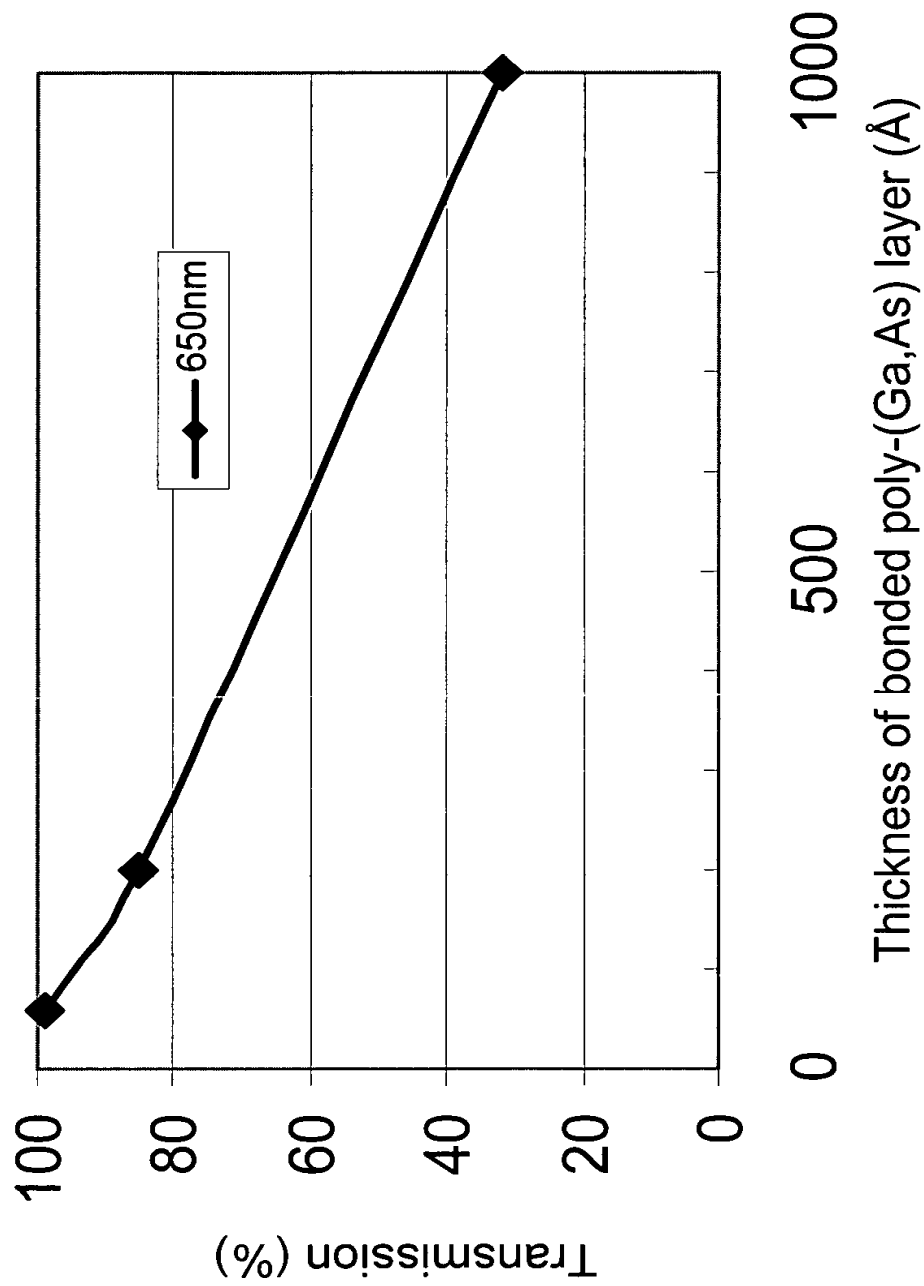


Fig. 16

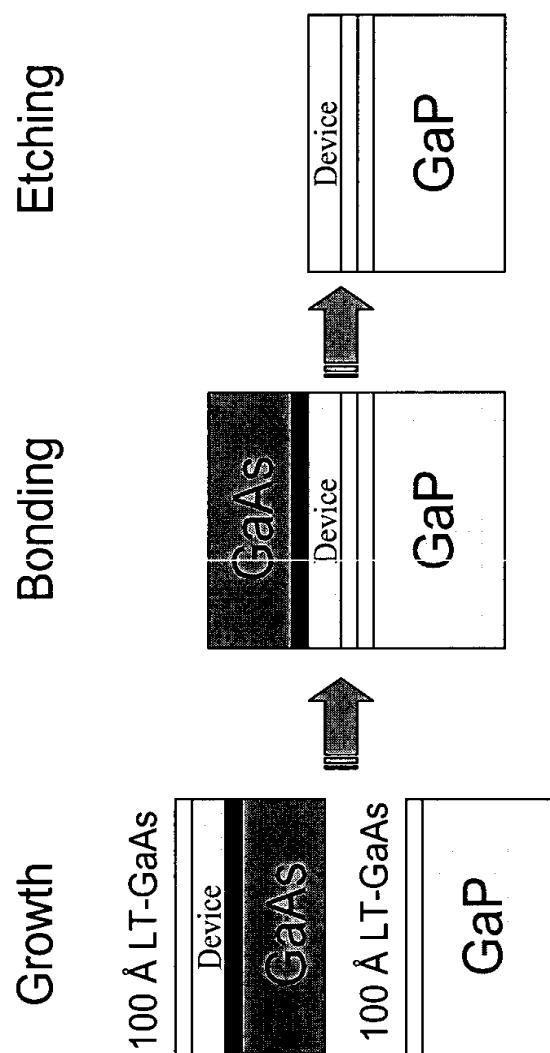


Fig. 17

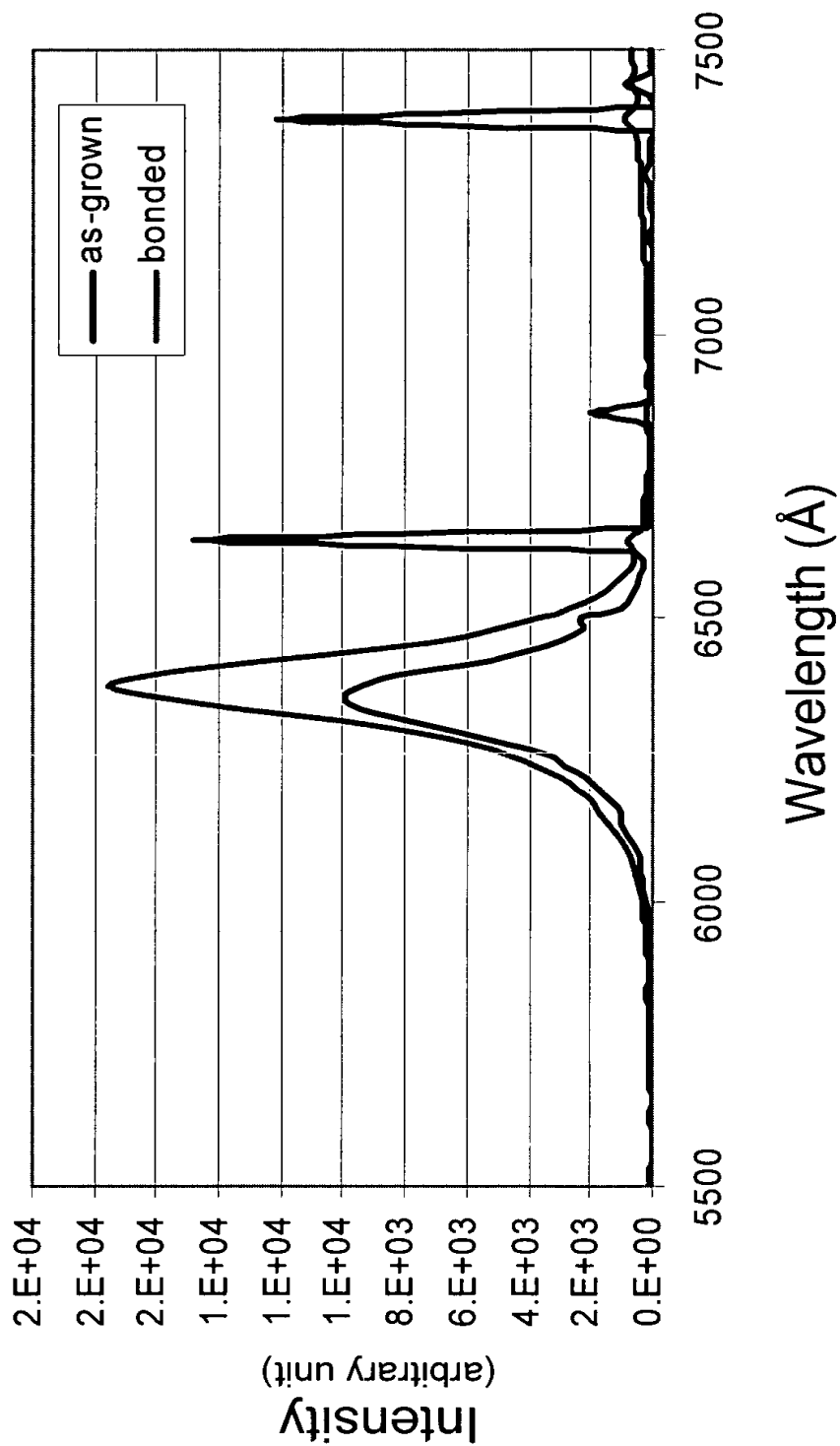


Fig. 18

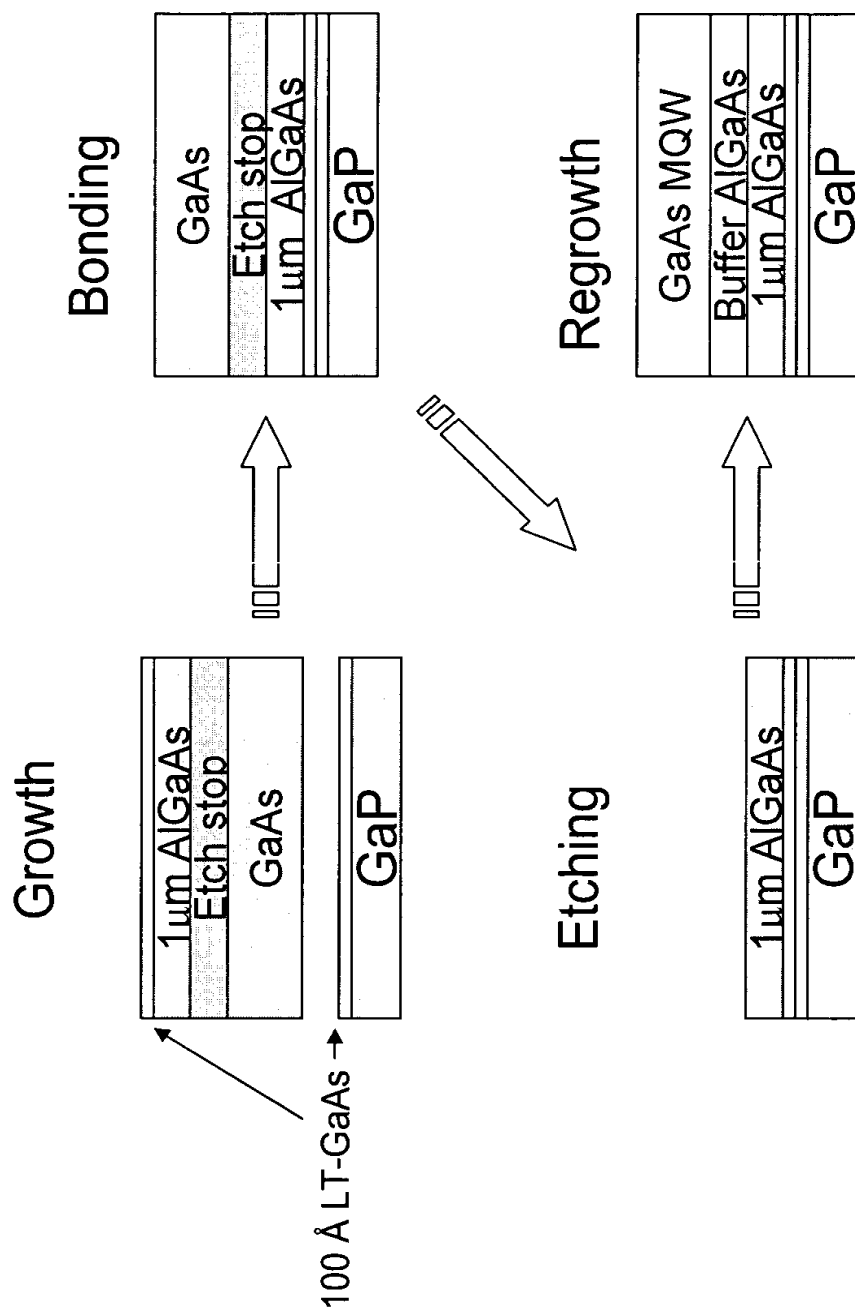


Fig. 19

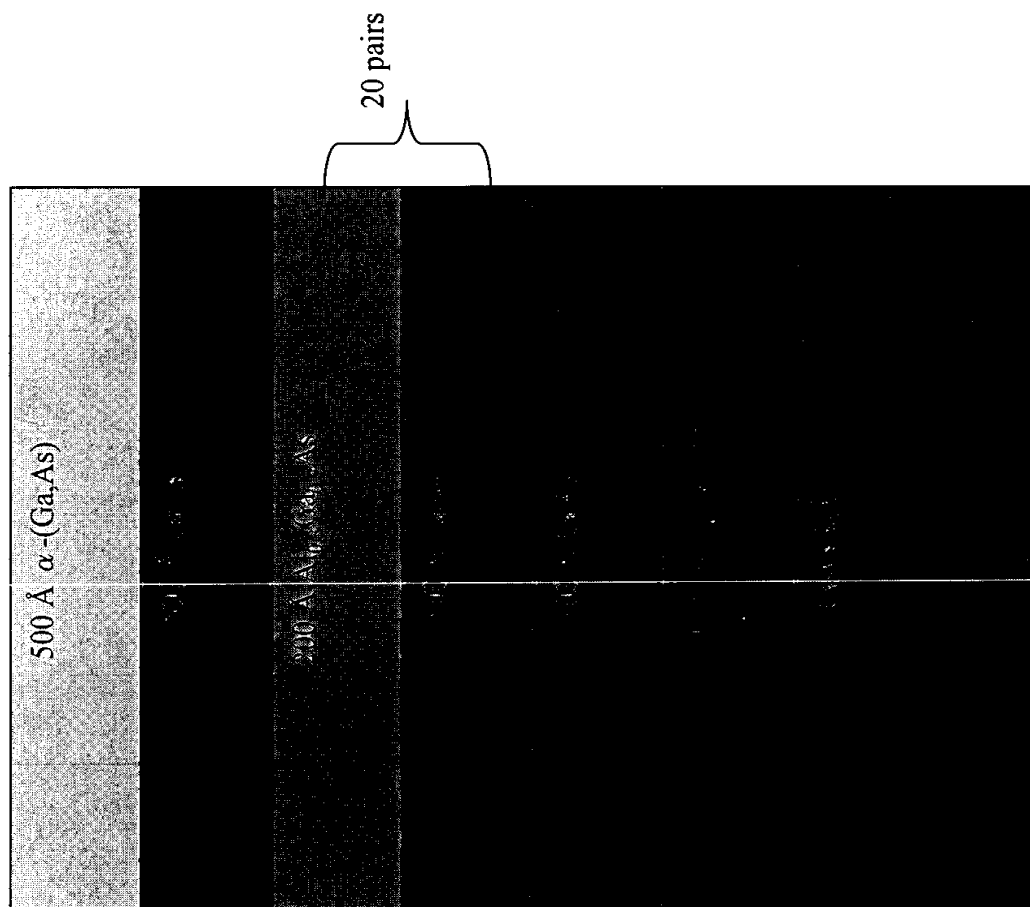


Fig. 20(a)

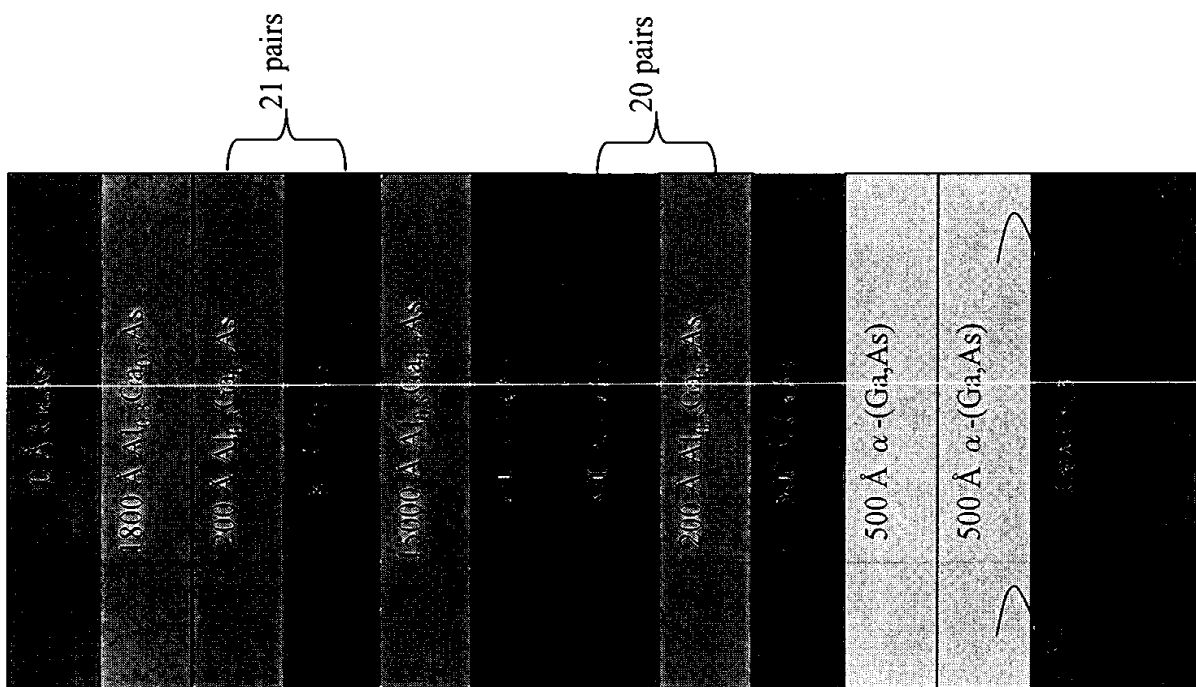


Fig. 20(b)

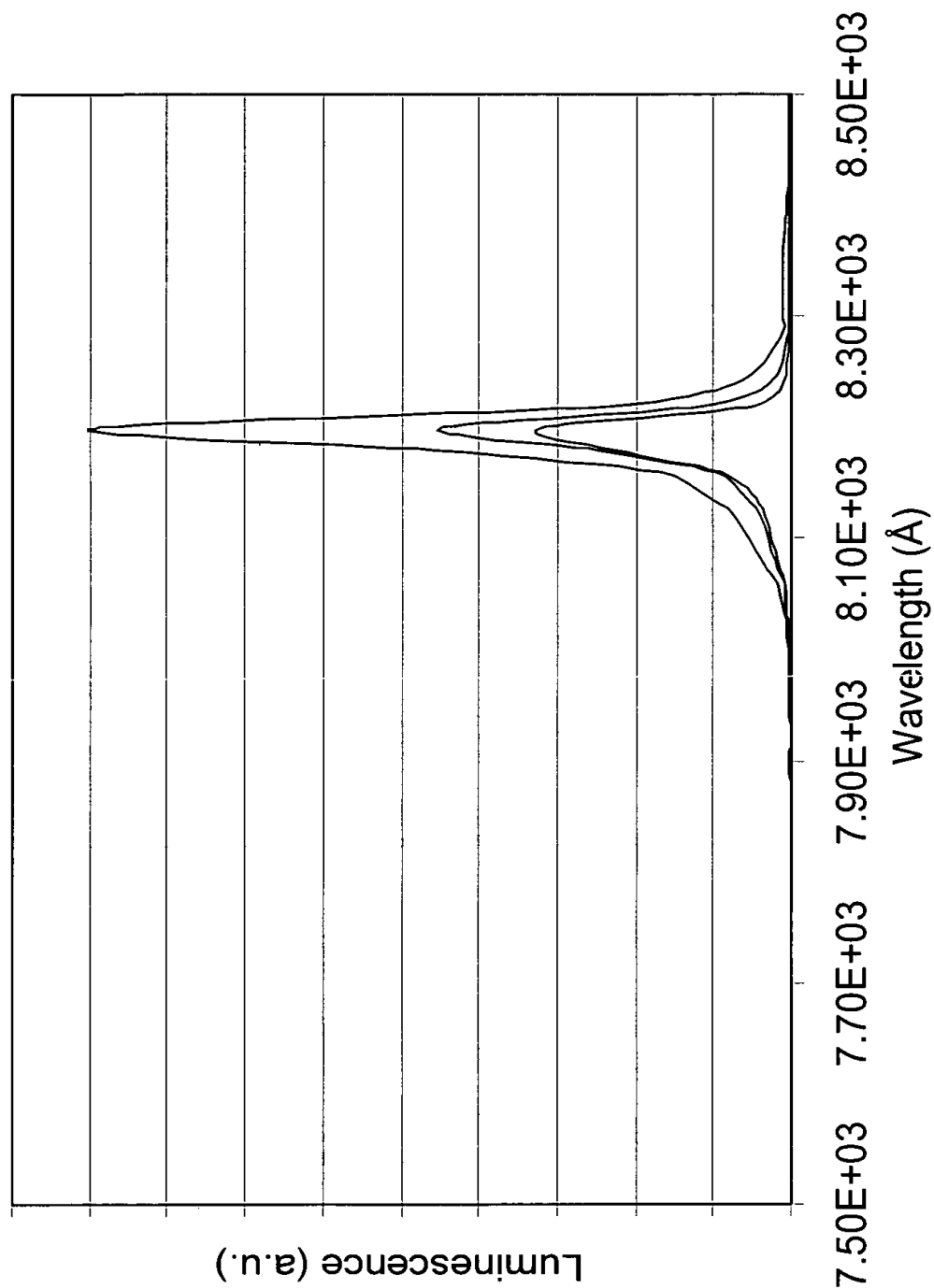


Fig. 21

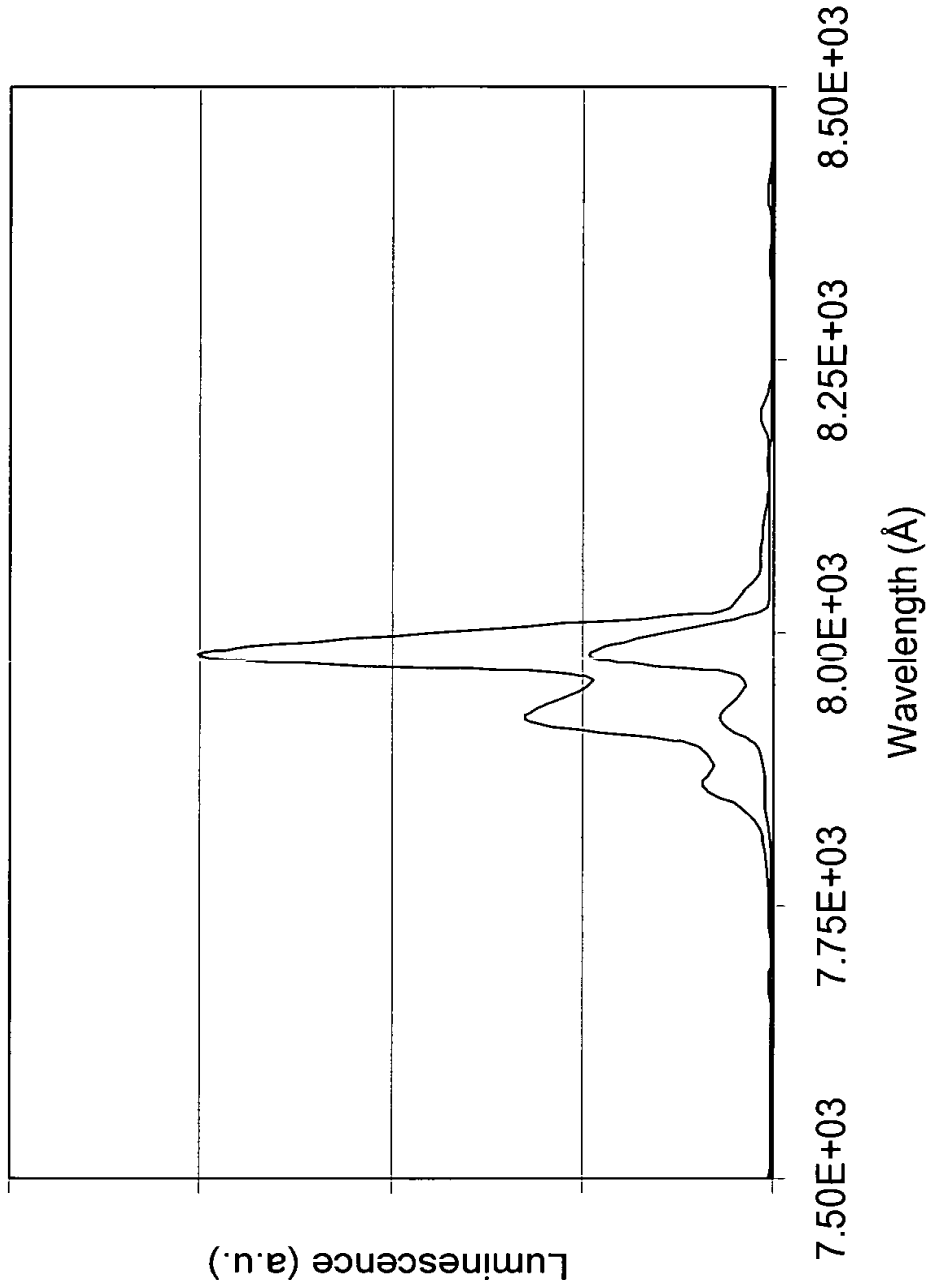


Fig. 22

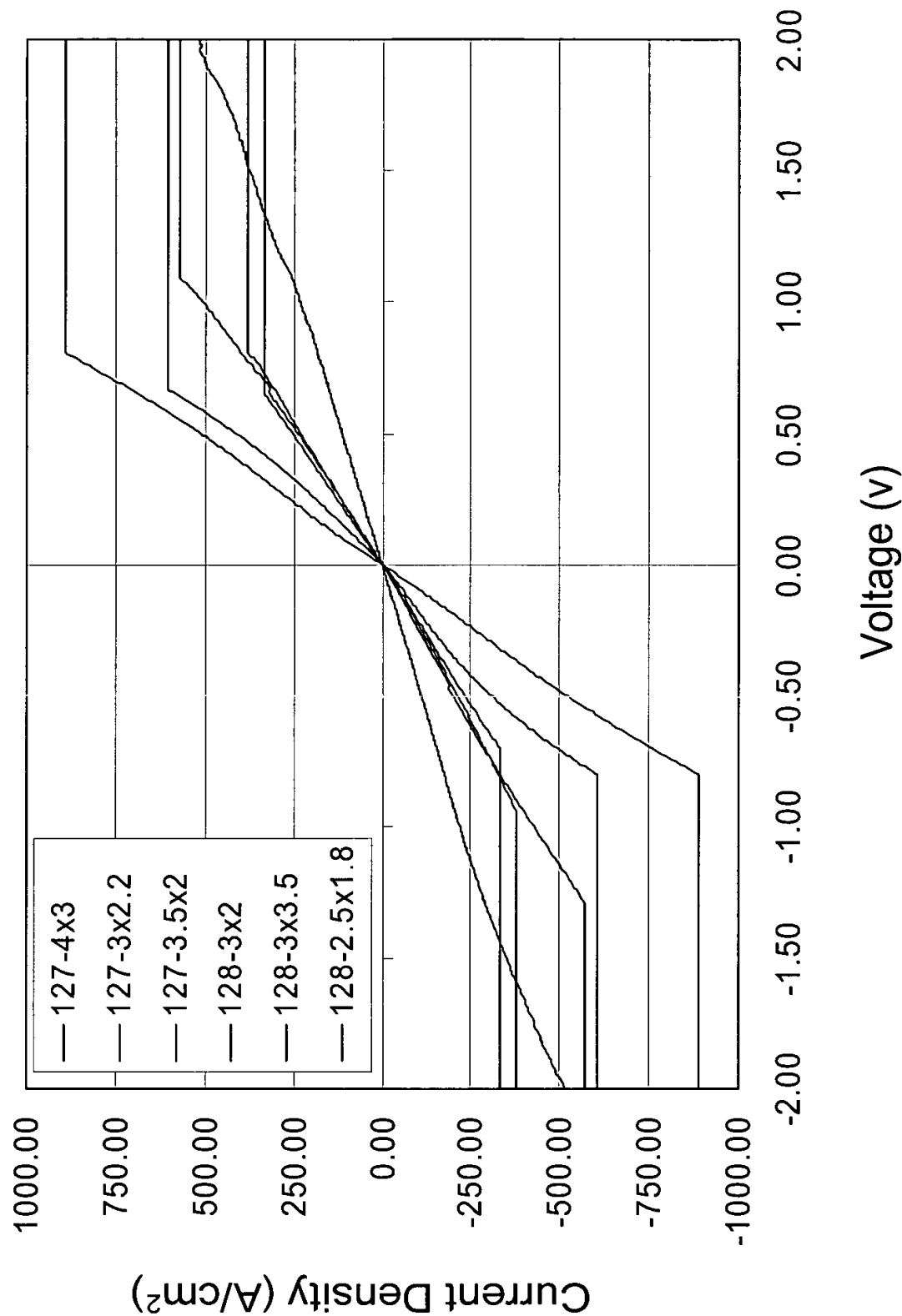


Fig. 23